

SEMIPONT™ 5

Bridge Rectifier

SKDT 115

Target Data

Features

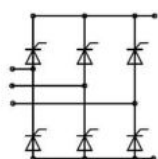
- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper board (low R_{th})
- Low resistance in steady-state and high reliability
- High surge currents
- Glass passivated thyristor chips
- Up to 1600 V reverse voltage
- UL -recognized, file no. E 63 532

Typical Applications*

- DC and AC drives
- Controlled field rectifier for DC motors
- Controlled battery charger

| V_{RSM} V | V_{RRM}, V_{DRM} V | $I_D = 110$ A (full conduction) ($T_s = 80$ °C) |
|----------------|-------------------------|---|
| 1300 | 1200 | SKDT 115/12 |
| 1700 | 1600 | SKDT 115/16 |

| Symbol | Conditions | Values | Units |
|--------------------|---|----------------|--------------------------------------|
| I_D | $T_s = 80$ °C | 110 | A |
| I_{TSM}, I_{FSM} | $T_{vj} = 25$ °C; 10 ms $T_{vj} = 125$ °C; 10 ms | 1050 950 | A A |
| i^2t | $T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 125$ °C; 8,3 ... 10 ms | 5500 4500 | A ² s A ² s |
| V_T, V_F | $T_{vj} = 25$ °C; $I_T, I_F = 120$ A | max. 1,8 | V |
| $V_{T(TO)}$ | $T_{vj} = 125$ °C; | max. 1,1 | V |
| r_T | $T_{vj} = 125$ °C | max. 6 | mΩ |
| I_{DD}, I_{RD} | $T_{vj} = 125$ °C; $V_{DD} = V_{DRM}, V_{RD} = V_{RRM}$ | max. 20 | mA |
| t_{gd} | $T_{vj} = 25$ °C; $I_G = A$; $di_G/dt = A/\mu s$ | | μs |
| t_{gr} | $V_D = \cdot V_{DRM}$ | | μs |
| $(dv/dt)_{cr}$ | $T_{vj} = 125$ °C | max. 500 | V/μs |
| $(di/dt)_{cr}$ | $T_{vj} = 125$ °C; $f = 50...60$ Hz | max. 50 | A/μs |
| t_q | $T_{vj} = 125$ °C; typ. | 150 | μs |
| I_H | $T_{vj} = 25$ °C; typ. / max. | - / 200 | mA |
| I_L | $T_{vj} = 25$ °C; $R_G = 33$ Ω | - / 400 | mA |
| V_{GT} | $T_{vj} = 25$ °C; d.c. | min. 3 | V |
| I_{GT} | $T_{vj} = 25$ °C; d.c. | min. 150 | mA |
| V_{GD} | $T_{vj} = 125$ °C; d.c. | max. 0,25 | V |
| I_{GD} | $T_{vj} = 125$ °C; d.c. | max. 5 | mA |
| $R_{th(j-s)}$ | per thyristor | 0,84 | K/W K/W K/W |
| T_{vj} | | - 40 ... + 125 | °C |
| T_{stg} | | - 40 ... + 125 | °C |
| T_{solder} | terminals | 260 | °C |
| V_{isol} | a. c. 50 Hz; r.m.s.; 1 s / 1 min. | 3600 (3000) | V |
| M_s | to heatsink | 2,5 | Nm |
| M_t | | | Nm |
| m | approx. | 75 | g |
| Case | | G 58 | |



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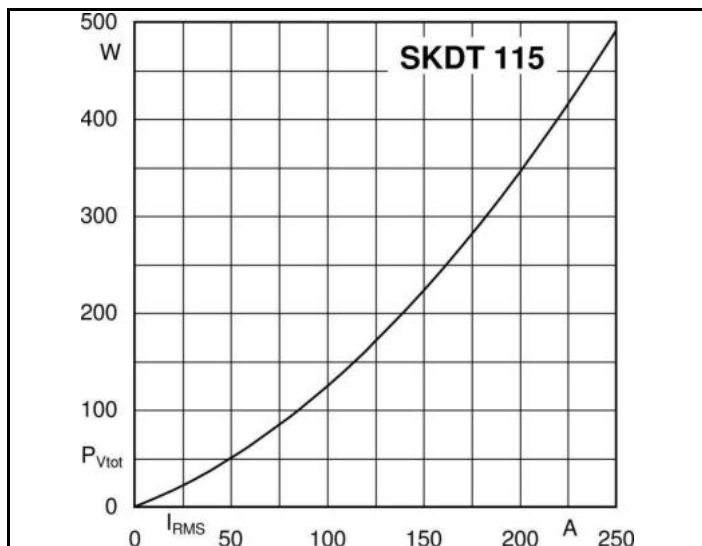


Fig. 1 Power dissipation vs. r.m.s. current

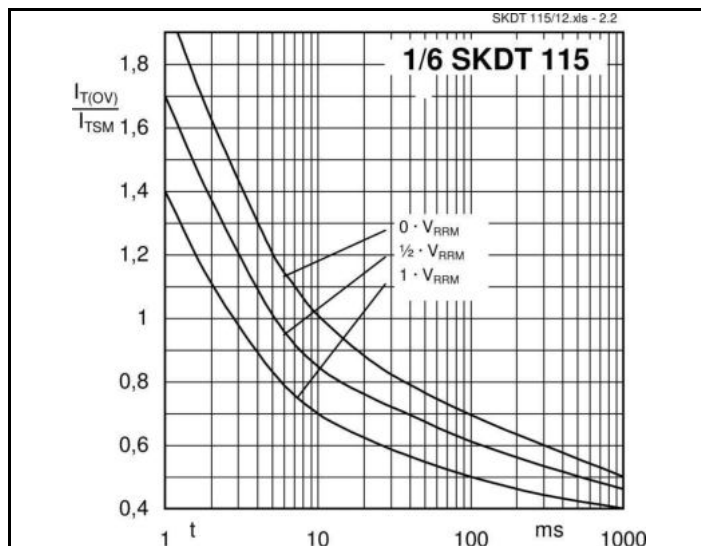


Fig. 2 Surge overload current vs. time

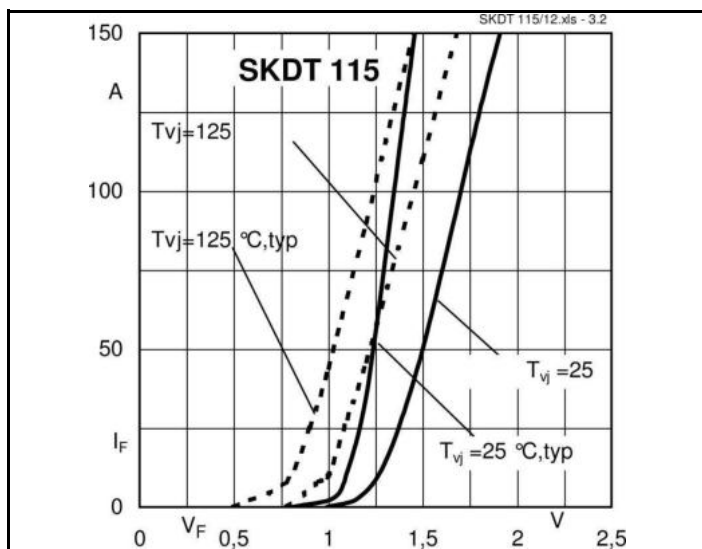


Fig. 3 Single thyristor on-state characteristic

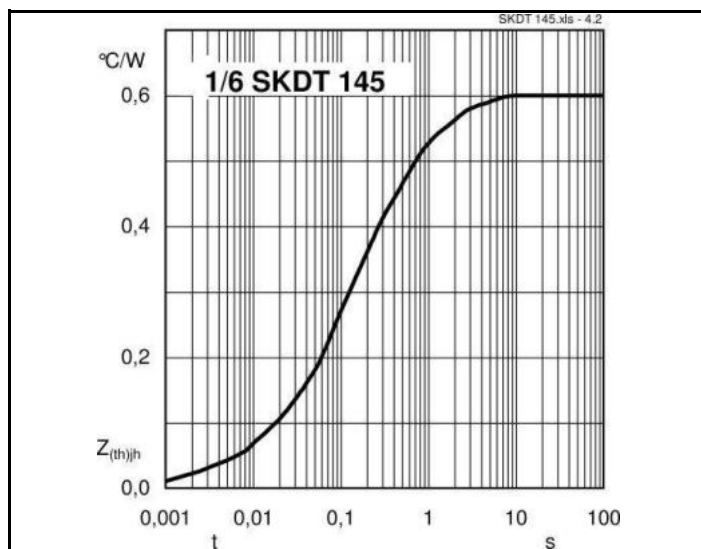


Fig. 4 Transient thermal impedance vs. time

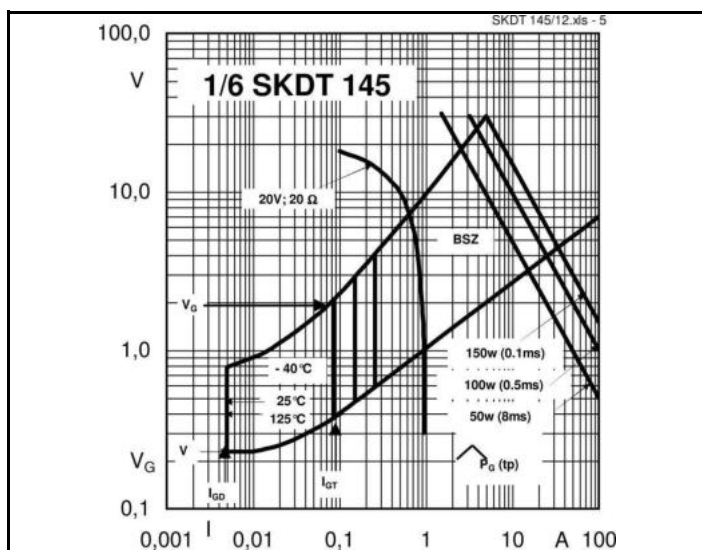
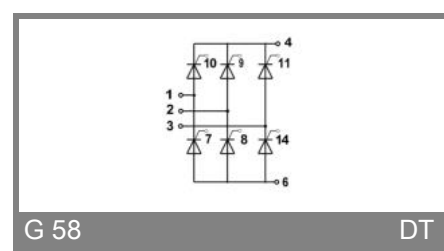
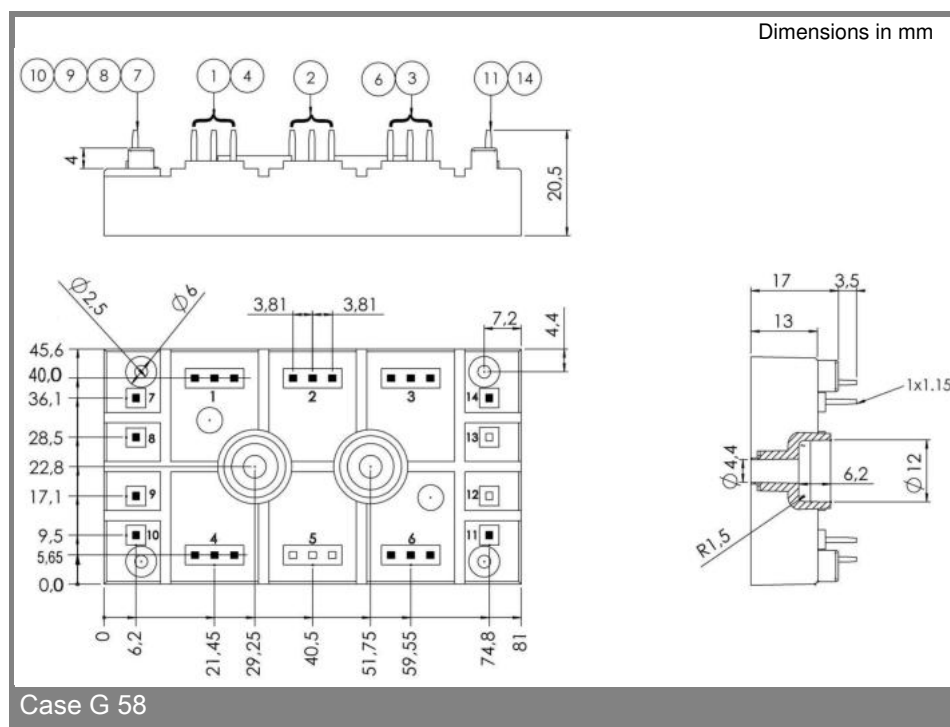


Fig. 5 Gate trigger characteristic



G 58

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Case G 58

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.